IN THE CLAIMS:

- 1-72. (Cancelled).
- 73. (Previously Presented) A thin film transistor comprising:
 a crystalline semiconductor island over a substrate having an insulating surface;

source and drain regions in said semiconductor island;
a channel forming region between said source and drain regions;
a gate insulating film adjacent to at least said channel forming region;
a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said channel forming region has no grain boundary, and wherein said semiconductor island includes a spin density not higher than 1 x 10^{17} cm⁻³,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³.

- 74. (Previously Presented) A thin film transistor according to claim 73 wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 75. (Previously Presented) A thin film transistor according to claim 74 wherein said material is included in said semiconductor island at a concentration not higher than 5 x 10^{19} cm⁻³.
- 76. (Previously Presented) A thin film transistor according to claim 73 wherein said semiconductor island includes the point defect of 1×10^{16} cm⁻³ or more, and the one of hydrogen and halogen element for neutralizing the point defect at a concentration of 1×10^{15} to 1×10^{20} cm⁻³.

- 77. (Previously Presented) A thin film transistor according to claim 73 wherein said semiconductor island includes the spin density not lower than 1×10^{15} cm⁻³.
- 78. (Previously Presented) A thin film transistor according to claim 73 wherein said semiconductor island is a silicon island.
- 79. (Previously Presented) A thin film transistor according to claim 73 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 80. (Previously Presented) A thin film transistor comprising:
 a crystalline semiconductor island on an insulating surface;
 source and drain regions in said semiconductor island;
 a channel forming region between said source and drain regions;
 a gate insulating film on at least said channel forming region;
 a gate electrode over said channel forming region having said gate insulating film therebetween,

wherein said channel forming region has no grain boundary, and wherein said semiconductor island includes a point defect of $1 \times 10^{16} \text{ cm}^{-3}$ or more, and at least one of hydrogen and halogen element at concentration not higher than $1 \times 10^{20} \text{ cm}^{-3}$.

- 81. (Previously Presented) A thin film transistor according to claim 80 wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 82. (Previously Presented) A thin film transistor according to claim 80 wherein said material is included in said semiconductor island at a concentration not higher than 5 x 10^{19} cm⁻³.

- 83. (Previously Presented) A thin film transistor according to claim 80 wherein said semiconductor island includes said one of hydrogen and halogen element for neutralizing the point defect at a concentration not lower than 1×10^{15} cm⁻³.
- 84. (Previously Presented) A thin film transistor according to claim 80 wherein said semiconductor island includes a spin density of 1×10^{15} to 1×10^{17} cm⁻³.
- 85. (Previously Presented) A thin film transistor according to claim 80 wherein said semiconductor island is a silicon island.
- 86. (Previously Presented) A thin film transistor according to claim 80 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 87. (Previously Presented) A semiconductor device comprising:
 a crystalline semiconductor island on an insulating surface;
 source and drain regions in said semiconductor island;
 a channel forming region between said source and drain regions;
 a gate insulating film adjacent to at least said channel forming region;
 a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said crystalline semiconductor island is formed in a monodomain region which contains no grain boundary,

wherein at least one of hydrogen and halogen element is contained at concentration not higher than 1×10^{20} cm⁻³,

wherein the semiconductor device includes a p-channel thin film transistor having a mobility in a range of 200-400 cm²/Vs.

88. (Previously Presented) A device according to claim 87, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.

- 89. (Previously Presented) A device according to claim 88, wherein said material is included in said semiconductor island at a concentration not higher than 5×10^{19} cm⁻³.
- 90. (Previously Presented) A device according to claim 87, wherein said semiconductor island is a silicon island.
- 91. (Previously Presented) A device according to claim 87, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 92. (Previously Presented) A device according to claim 87, wherein said monodomain region has a grain size of 50 μm or more.
- 93. (Previously Presented) A semiconductor device comprising:
 a crystalline semiconductor island on an insulating surface;
 source and drain regions in said semiconductor island;
 a channel forming region between said source and drain regions;
 a gate insulating film adjacent to at least said channel forming region;
 a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said channel forming region is formed in a monodomain region which contains no grain boundary,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³,

wherein the semiconductor device includes at least one n-channel thin film transistor having a mobility in a range of $500-1000 \text{ cm}^2/\text{Vs}$.

94. (Previously Presented) A device according to claim 93, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.

- 95. (Currently Amended) A device according to claim [[94]] $\underline{93}$, wherein said material is included in said semiconductor island at a concentration not higher than 5 x 10^{19} cm⁻³.
- 96. (Previously Presented) A device according to claim 93, wherein said semiconductor island is a silicon island.
- 97. (Previously Presented) A device according to claim 93, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 98. (Previously Presented) A device according to claim 93, wherein said monodomain region has a grain size of 50 µm or more.
- 99. (Previously Presented) A semiconductor device comprising:

 a p-channel thin film transistor;

 an n-channel thin film transistor;

 each of said p-channel thin film transistor and said n-channel thin film transistor comprising:

a crystalline semiconductor island on an insulating surface;
source and drain regions in said semiconductor island;
a channel forming region between said source and drain regions;
a gate insulating film adjacent to at least said channel forming region;
a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said crystalline semiconductor island is formed in a monodomain region which contains no grain boundary,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³.

4)

- 100. (Previously Presented) A device according to claim 99, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 101. (Previously Presented) A device according to claim 100, wherein said material is included in said semiconductor island at a concentration not higher than 5×10^{19} cm⁻³.
- 102. (Previously Presented) A device according to claim 99, wherein said semiconductor island is a silicon island.
- 103. (Previously Presented) A device according to claim 99, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 104. (Previously Presented) A device according to claim 99, wherein said monodomain region has a grain size of 50 μm or more.
- 105. (Previously Presented) A semiconductor device comprising:

 a p-channel thin film transistor;

 an n-channel thin film transistor;

 each of said p-channel thin film transistor and said n-channel thin film transistor comprising:
- a crystalline semiconductor island on an insulating surface;
 source and drain regions in said semiconductor island;
 a channel forming region between said source and drain regions;
 a gate insulating film adjacent to at least said channel forming region;
 a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,
- wherein said crystalline semiconductor island includes carbon at a concentration not higher than 5×10^{18} cm⁻³,

wherein said channel forming region is formed in a monodomain region which contains no grain boundary,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³.

- 106. (Previously Presented) A device according to claim 105, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 107. (Previously Presented) A device according to claim 106, wherein said material is included in said semiconductor island at a concentration not higher than 5×10^{19} cm⁻³.
- 108. (Previously Presented) A device according to claim 105, wherein said semiconductor island is a silicon island.
- 109. (Previously Presented) A device according to claim 105, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 110. (Previously Presented) A device according to claim 105, wherein said monodomain region has a grain size of 50 μ m or more.
 - 111. (Previously Presented) A semiconductor device comprising:
 an active matrix circuit portion including at least a first thin film transistor;
 a driving circuit portion including at least a second thin film transistor;
 said second thin film transistor comprising:
 a crystalline semiconductor island on an insulating surface;
 source and drain regions in said semiconductor island;
 a channel forming region between said source and drain regions;
 a gate insulating film adjacent to at least said channel forming region;

a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said crystalline semiconductor island is formed in a monodomain region which contains no grain boundary,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³.

- 112. (Previously Presented) A device according to claim 111, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 113. (Previously Presented) A device according to claim 112, wherein said material is included in said semiconductor island at a concentration not higher than 5×10^{19} cm⁻³.
- 114. (Previously Presented) A device according to claim 111, wherein said semiconductor island is a silicon island.
- 115. (Previously Presented) A device according to claim 111, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 116. (Previously Presented) A device according to claim 111, wherein said monodomain region has a grain size of 50 µm or more.

117-122. (Cancelled).

123. (Previously Presented) A semiconductor device comprising:
a crystalline semiconductor island on an insulating surface;
source and drain regions in said semiconductor island;
a channel forming region between said source and drain regions;
a gate insulating film adjacent to at least said channel forming region;
a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³,

wherein said crystalline semiconductor island is formed in a monodomain region which contains no grain boundary,

wherein said semiconductor device has a S value of 0.03-0.3,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³,

wherein the semiconductor device includes at least one selected from the group consisting of a p-channel thin film transistor and an n-channel thin film transistor,

wherein the p-channel thin film transistor has a mobility in a range of 200-400 $\,\mathrm{cm^2/Vs}$ while the n-channel thin film transistor has a mobility in a range of 500-1000 $\,\mathrm{cm^2/Vs}$.

- 124. (Previously Presented) A device according to claim 123, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 125. (Previously Presented) A device according to claim 124, wherein said material is included in said semiconductor island at a concentration not higher than 5×10^{19} cm⁻³.
- 126. (Previously Presented) A device according to claim 123, wherein said semiconductor island is a silicon island.
- 127. (Previously Presented) A device according to claim 123, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.
- 128. (Previously Presented) A device according to claim 123, wherein said monodomain region has a grain size of $50 \mu m$ or more.
- 129. (Previously Presented) A semiconductor device comprising:
 a crystalline semiconductor island on an insulating surface;

source and drain regions in said semiconductor island;

- a channel forming region between said source and drain regions;
- a gate insulating film adjacent to at least said channel forming region;
- a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,

wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³,

wherein said channel forming region is formed in a monodomain region which contains no grain boundary,

wherein said semiconductor device has a S value of 0.03-0.3,

wherein said crystalline semiconductor island includes at least one of hydrogen and halogen element at concentration not higher than 1×10^{20} cm⁻³,

wherein the semiconductor device includes at least one selected from the group consisting of a p-channel thin film transistor and an n-channel thin film transistor, wherein the p-channel thin film transistor has a mobility in a range of 200-400 cm²/Vs while the n-channel thin film transistor has a mobility in a range of 500-1000 cm²/Vs.

- 130. (Previously Presented) A device according to claim 129, wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.
- 131. (Previously Presented) A device according to claim 130, wherein said material is included in said semiconductor island at a concentration not higher than 5 x 10^{19} cm⁻³.
- 132. (Previously Presented) A device according to claim 129, wherein said semiconductor island is a silicon island.
- 133. (Previously Presented) A device according to claim 129, wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than 1×10^{16} cm⁻³, and oxygen at a concentration not lower than 1×10^{17} cm⁻³.

- 134. (Previously Presented) A device according to claim 129, wherein said monodomain region has a grain size of 50 μm or more.
- 135. (Previously Presented) A thin film transistor according to claim 73, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 136. (Previously Presented) A thin film transistor according to claim 80, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 137. (Previously Presented) A device according to claim 87, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 138. (Previously Presented) A device according to claim 93, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 139. (Previously Presented) A device according to claim 99, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 140. (Previously Presented) A device according to claim 105, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 141. (Previously Presented) A device according to claim 111, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).

142. (Cancelled).

- 143. (Previously Presented) A device according to claim 123, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 144. (Previously Presented) A device according to claim 129, wherein each of the concentrations of carbon, nitrogen and oxygen is measured by secondary ion mass spectroscopy (SIMS).
- 145. (Previously Presented) The thin film transistor according to claim 73 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³, and oxygen at a concentration not higher than 5×10^{19} cm⁻³.
- 146. (Previously Presented) The thin film transistor according to claim 73 wherein the thin film transistor is one of a p-channel thin film transistor having a mobility in a range of 200-400 cm²/Vs and an n-channel thin film transistor having a mobility in a range of 500-1000 cm²/Vs.
- 147. (Previously Presented) The thin film transistor according to claim 80 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³, and oxygen at a concentration not higher than 5×10^{19} cm⁻³.
- 148. (Previously Presented) The thin film transistor according to claim 80 wherein the thin film transistor is one of a p-channel thin film transistor having a mobility in a range of 200-400 cm²/Vs and an n-channel thin film transistor having a mobility in a range of 500-1000 cm²/Vs.

- 149. (Previously Presented) The semiconductor device according to claim 87 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³, and oxygen at a concentration not higher than 5×10^{19} cm⁻³.
- 150. (Previously Presented) The semiconductor device according to claim 93 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³, and oxygen at a concentration not higher than 5×10^{19} cm⁻³.
- 151. (Previously Presented) The semiconductor device according to claim 99 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³, and oxygen at a concentration not higher than 5×10^{19} cm⁻³.
- 152. (Previously Presented) The semiconductor device according to claim 99 wherein the p-channel thin film transistor has a mobility in a range of 200-400 cm²/Vs and the n-channel thin film transistor has a mobility in a range of 500-1000 cm²/Vs.
- 153. (Previously Presented) The semiconductor device according to claim 105 wherein the p-channel thin film transistor has a mobility in a range of 200-400 cm²/Vs and the n-channel thin film transistor has a mobility in a range of 500-1000 cm²/Vs.
- 154. (Previously Presented) The semiconductor device according to claim 111 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than 5×10^{18} cm⁻³.
- 155. (Previously Presented) The semiconductor device according to claim 111 wherein the second thin film transistor is one of a p-channel thin film transistor having a mobility in a range of 200-400 cm²/Vs and an n-channel thin film transistor having a mobility in a range of 500-1000 cm²/Vs.